

FEATURES

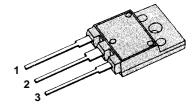
- Avalanche Rugged Technology
- Rugged Gate Oxide Technology
- Lower Input Capacitance
- Improved Gate Charge
- Extended Safe Operating Area
- Lower Leakage Current: 25 μ A (Max.) @ $V_{DS} = 800V$
- Lower $R_{DS(ON)}$: 0.746 Ω (Typ.)

$$BV_{DSS} = 800V$$

$$R_{DS(ON)} = 0.95\Omega$$

$$I_D = 10A$$

TO-3P



1. Gate 2. Drain 3. Source

ABSOLUTE MAXIMUM RATINGS

Symbol	Characteristics	Value	Units
V_{DSS}	Drain-to-Source Voltage	800	V
I_D	Continuous Drain Current ($T_C = 25^\circ C$)	10	A
	Continuous Drain Current ($T_C = 100^\circ C$)	6.3	
I_{DM}	Drain Current-Pulsed ①	40	A
V_{GS}	Gate-to-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy ②	533	mJ
I_{AR}	Avalanche Current ①	10	A
E_{AR}	Repetitive Avalanche Energy ①	28	mJ
dv/dt	Peak Diode Recovery dv/dt ③	2.0	V/ns
P_D	Total Power Dissipation ($T_C = 25^\circ C$)	280	W W/ $^\circ C$
	Linear Derating Factor	2.22	
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	$^\circ C$
T_L	Maximum Lead Temp. for Soldering Purposes, 1/8" from case for 5-seconds	300	

THERMAL RESISTANCE

Symbol	Characteristics	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	-	0.45	$^\circ C/W$
$R_{\theta CS}$	Case-to-Sink	0.24	-	
$R_{\theta JA}$	Junction-to-Ambient	-	40	

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Characteristics	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain-Source Breakdown Voltage	800	–	–	V	$V_{GS}=0V, I_D=250\mu A$
$\Delta BV/\Delta T_J$	Breakdown Voltage Temp. Coeff.	–	1.02	–	V/ $^\circ\text{C}$	$I_D=250\mu A$, See Fig 7
$V_{GS(th)}$	Gate Threshold Voltage	2.0	–	3.5	V	$V_{DS}=5V, I_D=250\mu A$
I_{GSS}	Gate-Source Leakage, Forward	–	–	100	nA	$V_{GS}=30V$
	Gate-Source Leakage, Reverse	–	–	–100		$V_{GS}= -30V$
I_{DSS}	Drain-to-Source Leakage Current	–	–	25	μA	$V_{DS}=800V$
		–	–	250		$V_{DS}=640V, T_C=125^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-State Resistance	–	–	0.95	Ω	$V_{GS}=10V, I_D=5A$ ④
g_{fs}	Forward Transconductance	–	8.43	–	S	$V_{DS}=50V, I_D=5A$ ④
C_{iss}	Input Capacitance	–	2700	3500	pF	$V_{GS}=0V, V_{DS}=25V$ $f=1\text{MHz}$ See Fig 5
C_{oss}	Output Capacitance	–	260	300		
C_{rss}	Reverse Transfer Capacitance	–	110	130		
$t_{d(on)}$	Turn-On Delay Time	–	29	70	ns	$V_{DD}=400V, I_D=10A$ $R_G=9.6\Omega$ See Fig 13 ④ ⑤
t_r	Rise Time	–	58	315		
$t_{d(off)}$	Turn-Off Delay Time	–	152	235		
t_f	Fall Time	–	48	105		
Q_g	Total Gate Charge	–	125	165	nC	$V_{DS}=640V, V_{GS}=10V$ $I_D=10A$ See Fig 6 & Fig 12 ④ ⑤
Q_{gs}	Gate-Source Charge	–	19.2	–		
Q_{gd}	Gate-Drain (Miller) Charge	–	45.4	–		

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristics	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current	–	–	10	A	Integral reverse pn-diode in the MOSFET
I_{SM}	Pulsed-Source Current ①	–	–	40		
V_{SD}	Diode Forward Voltage ④	–	–	1.4	V	$T_J=25^\circ\text{C}, I_S=10A, V_{GS}=0V$
t_{rr}	Reverse Recovery Time	–	620	–	ns	$T_J=25^\circ\text{C}, I_F=10A$
Q_{rr}	Reverse Recovery Charge	–	10.17	–	μC	$di_F/dt=100A/\mu\text{s}$ ④

Notes:

- ① Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
- ② $L=10\text{mH}, I_{AS}=10A, V_{DD}=50V, R_G=27\Omega$, Starting $T_J=25^\circ\text{C}$
- ③ $I_{SD} \leq 10A, di/dt \leq 200A/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J=25^\circ\text{C}$
- ④ Pulse Test: Pulse Width $\leq 250\mu\text{s}$, Duty Cycle $\leq 2\%$
- ⑤ Essentially Independent of Operating Temperature

Fig 1. Output Characteristics

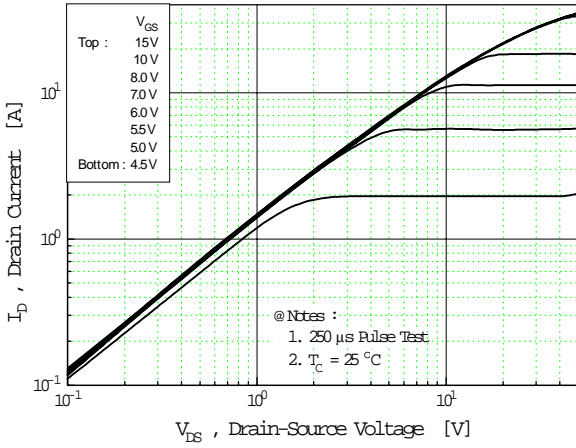


Fig 2. Transfer Characteristics

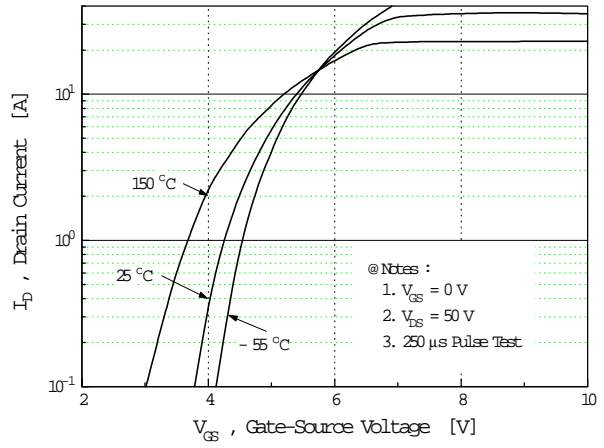


Fig 3. On-Resistance vs. Drain Current

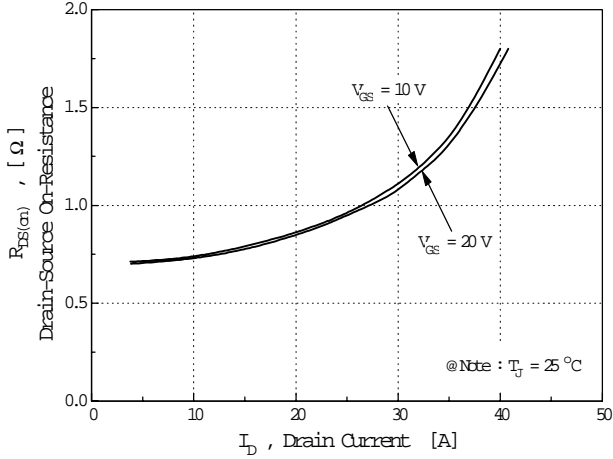


Fig 4. Source-Drain Diode Forward Voltage

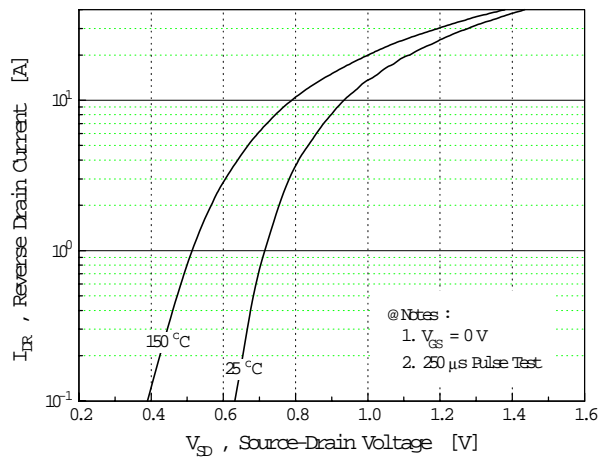


Fig 5. Capacitance vs. Drain-Source Voltage

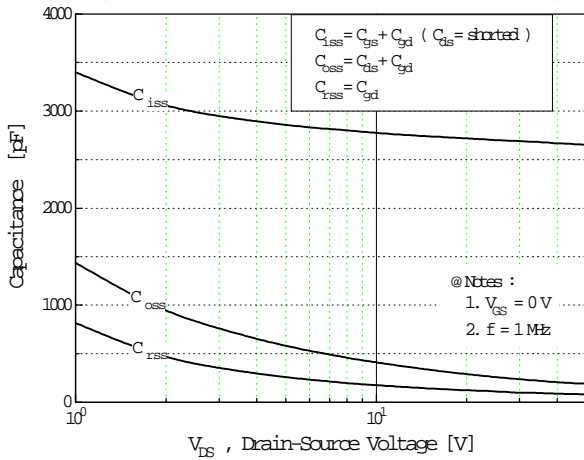


Fig 6. Gate Charge vs. Gate-Source Voltage

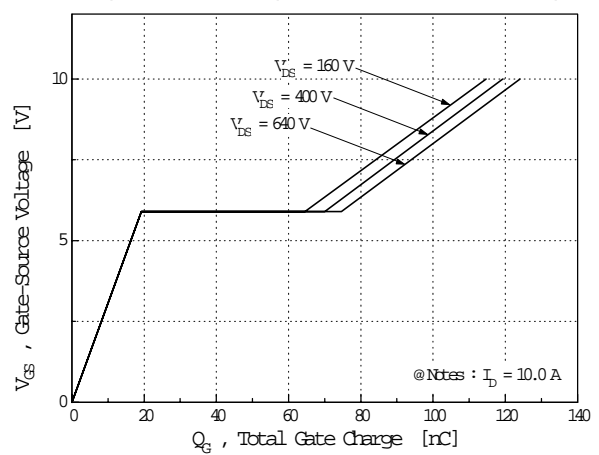


Fig 7. Breakdown Voltage vs. Temperature

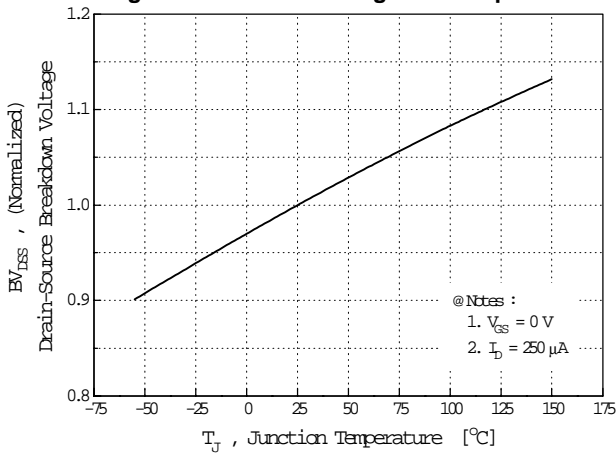


Fig 8. On-Resistance vs. Temperature

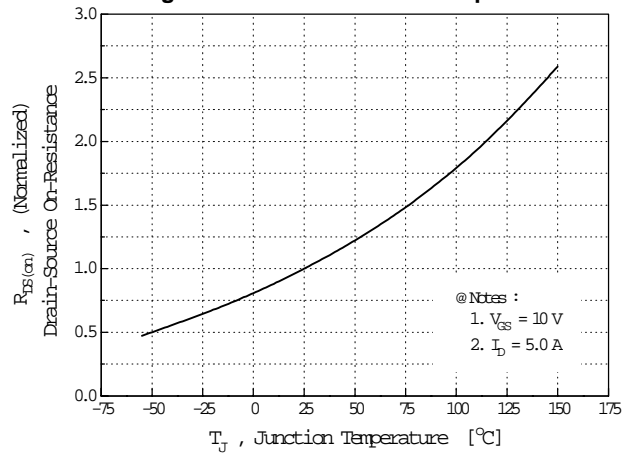


Fig 9. Max. Safe Operating Area

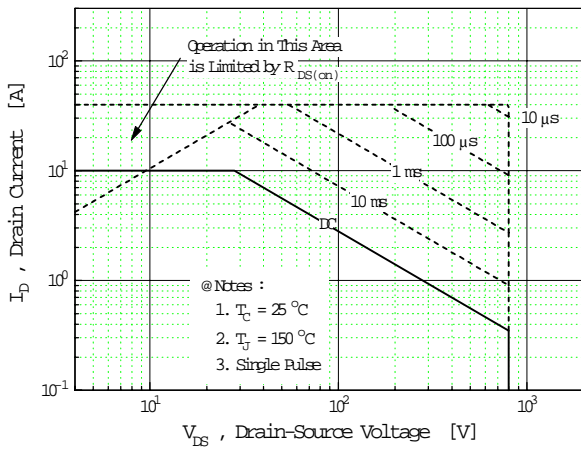


Fig 10. Max. Drain Current vs. Case Temperature

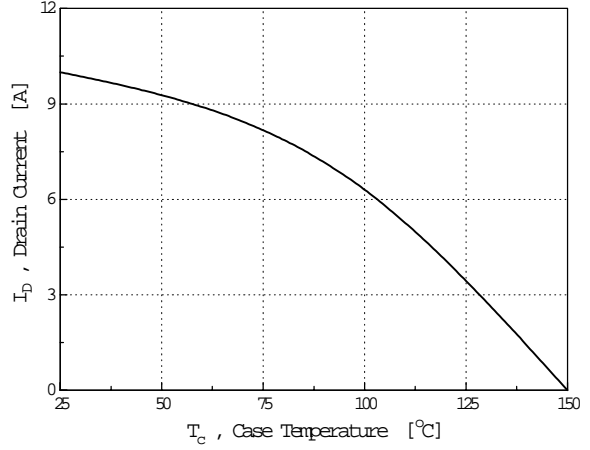


Fig 11. Thermal Response

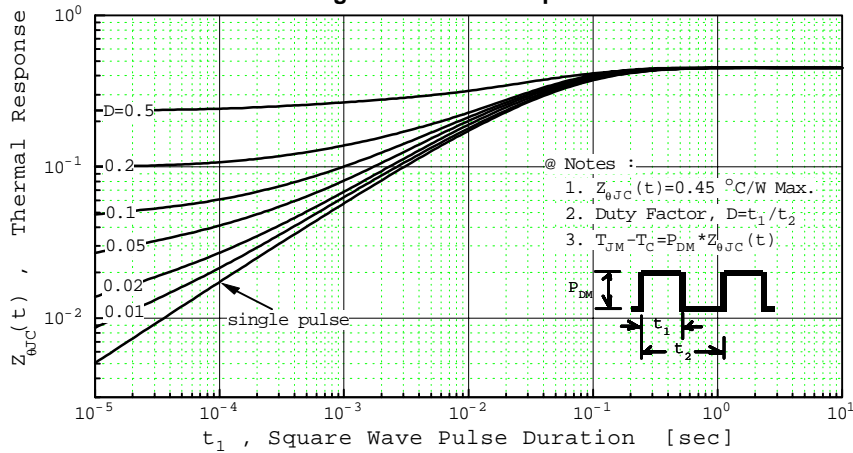


Fig 12. Gate Charge Test Circuit & Waveform

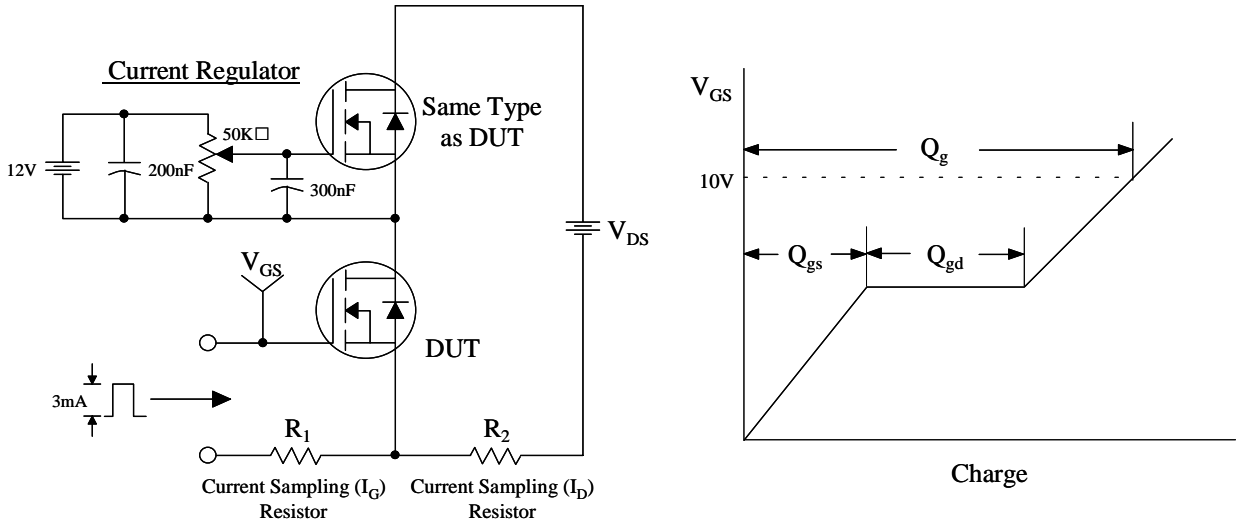


Fig 13. Resistive Switching Test Circuit & Waveforms

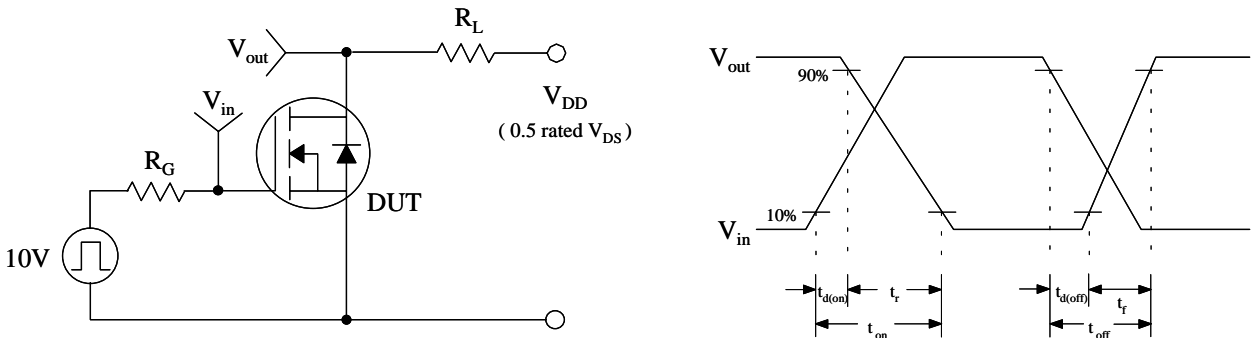


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

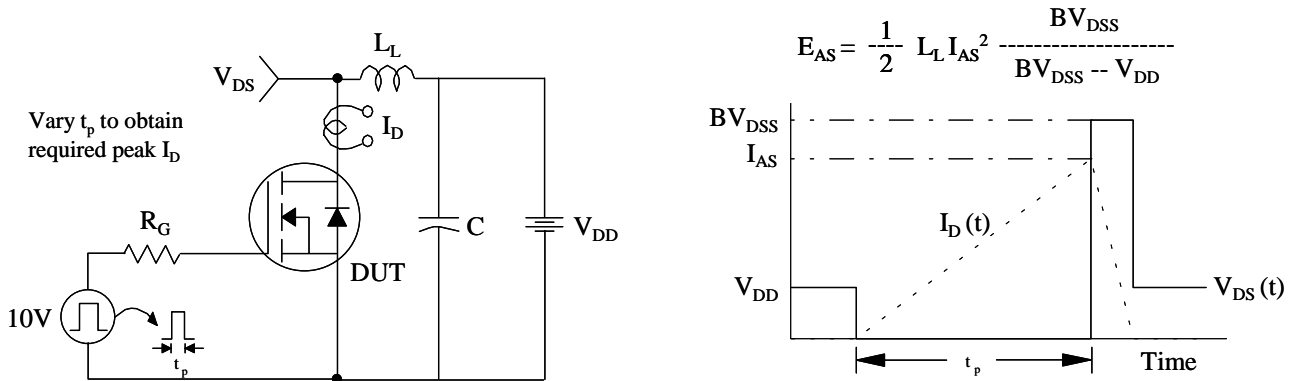
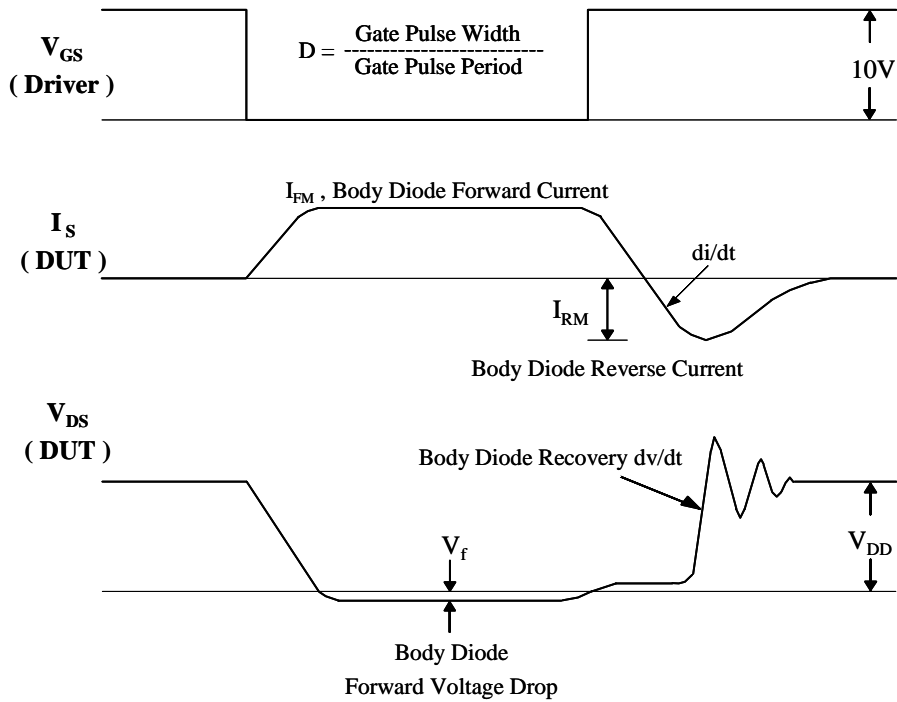
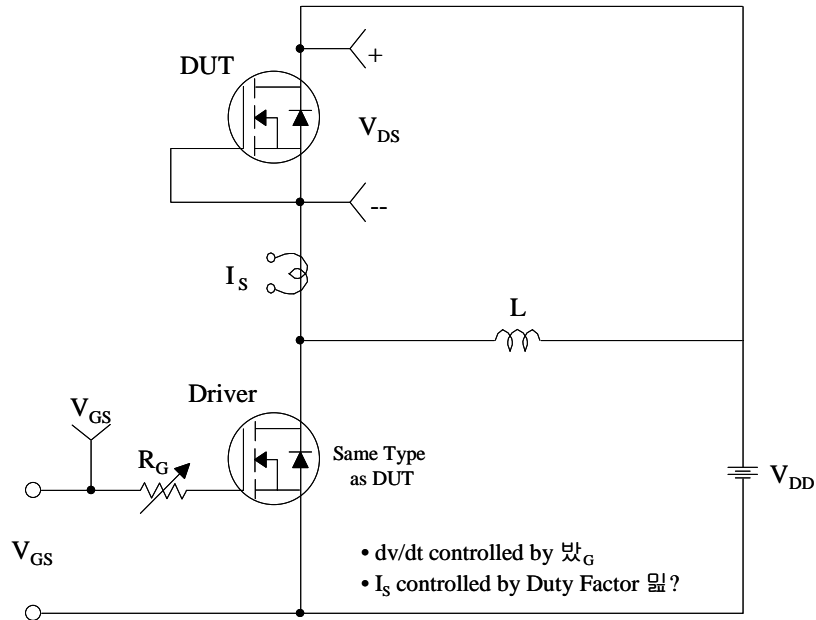


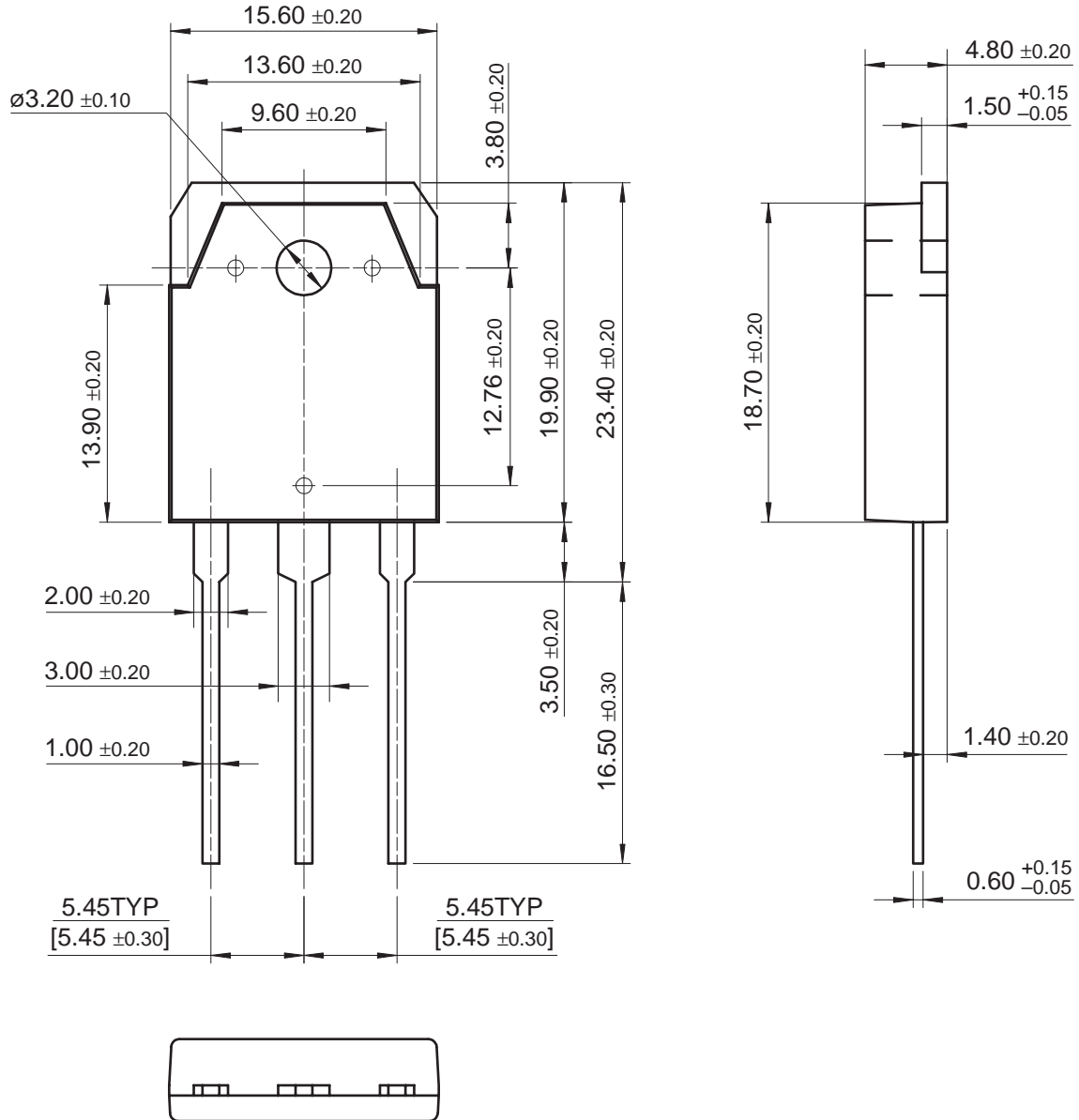
Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



TO-3P Package Dimensions



TO-3P (FS PKG CODE AF)



Dimensions in Millimeters

August 1999, Rev B

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